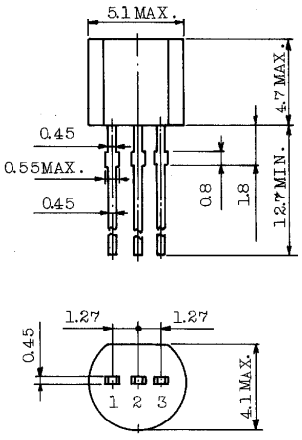
TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2SC2753

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATION.

Unit in mm

- Low Noise Figure, High Gain
- NF = 1.5dB, $|S_{21e}|^2$ = 16dB (f = 500MHz)
- NF = 1.7dB, $|S_{21e}|^2$ = 10.5dB (f = 1GHz)



1. BASE
2. EMITTER
3. COLLECTOR

JEDEC	TO-92
EIAJ	SC-43
TOSHIBA	2-5F1E

Weight : 0.21g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	17	V
Collector-Emitter Voltage	V_{CEO}	12	V
Emitter-Base Voltage	V_{EBO}	3	V
Collector Current	I_C	70	mA
Base Current	I_B	30	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	−55~125	°C

MICROWAVE CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Transition Frequency	f_T	V_{CE} = 10V, I_C = 20mA	—	5	—	GHz
Insertion Gain	$\|S_{21e}\|^2$(1)	V_{CE} = 10V, I_C = 20mA, f = 500MHz	—	16	—	dB
	$\|S_{21e}\|^2$(2)	V_{CE} = 10V, I_C = 20mA, f = 1GHz	—	10.5	—	dB
Noise Figure	NF(1)	V_{CE} = 10V, I_C = 5mA, f = 500MHz	—	1.5	—	dB
	NF(2)	V_{CE} = 10V, I_C = 5mA, f = 1GHz	—	1.7	—	dB

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB} = 10V, I_E = 0	—	—	1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB} = 1V, I_E = 0	—	—	1	μA
DC Current Gain	h_{FE}	V_{CE} = 10V, I_C = 20mA	30	—	180	—
Collector Output Capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz (Note)	—	1.1	—	pF
Reverse Transfer Capacitance	C_{re}		—	0.65	—	pF

Note : Cre is measured by 3 terminal method with Capacitance Bridge.

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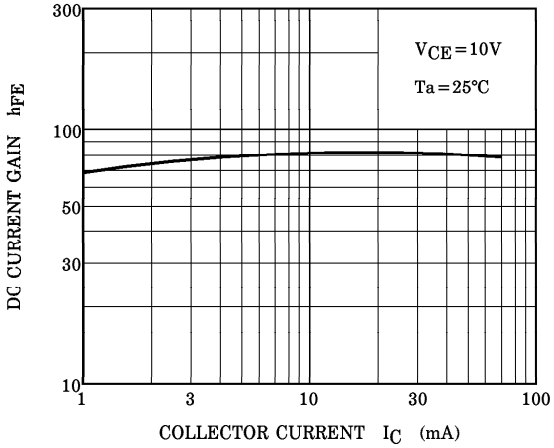
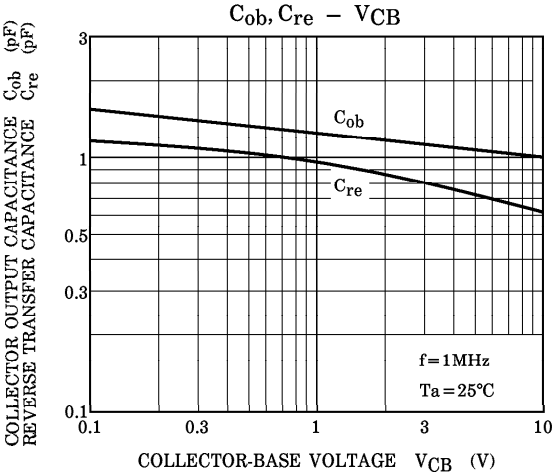
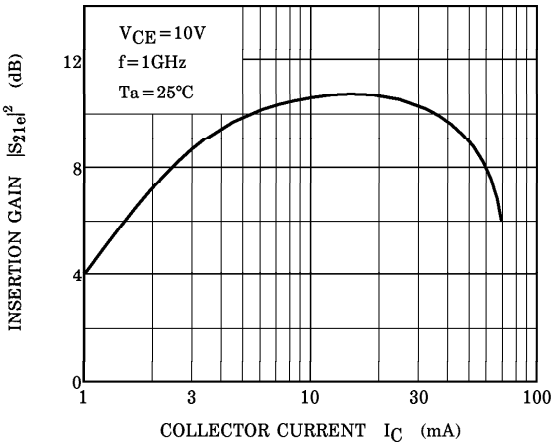
h_{FE} – I_C



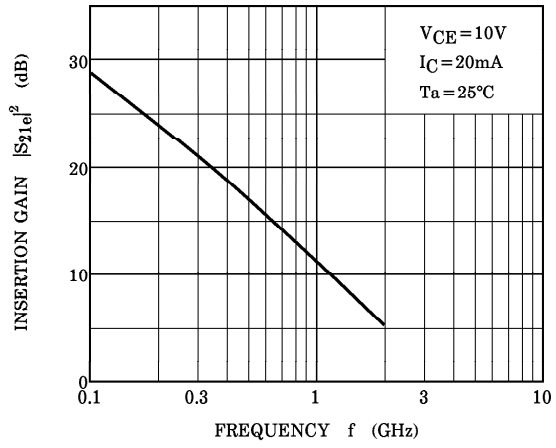
C_{ob}, C_{re} – V_{CB}



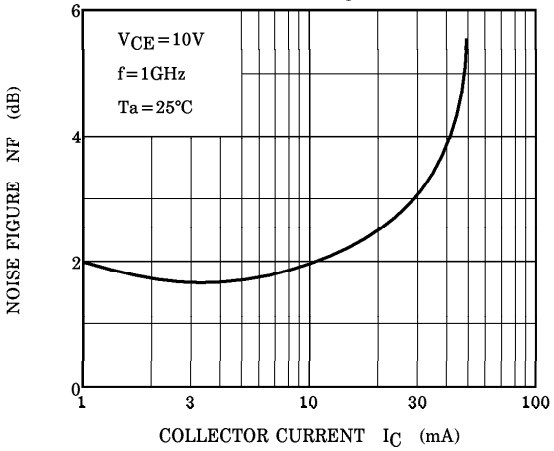
$|S_{21e}|^2$ – I_C



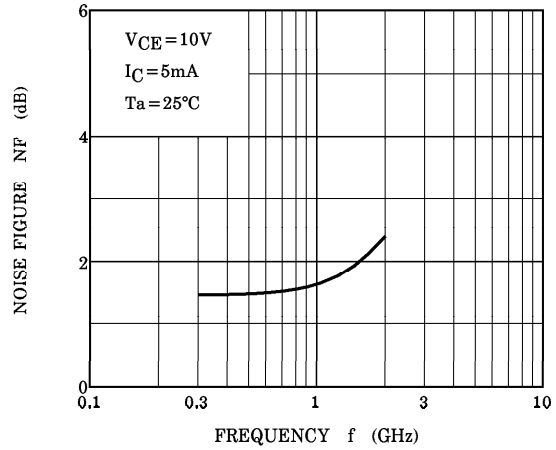
$|S_{21e}|^2$ – f



NF – I_C



NF – f



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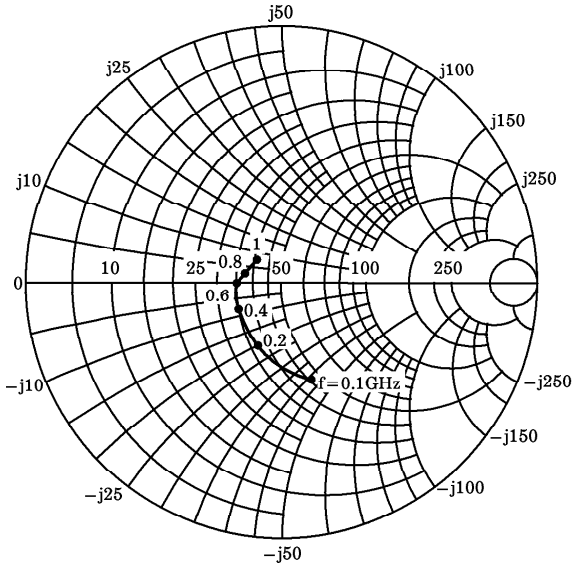
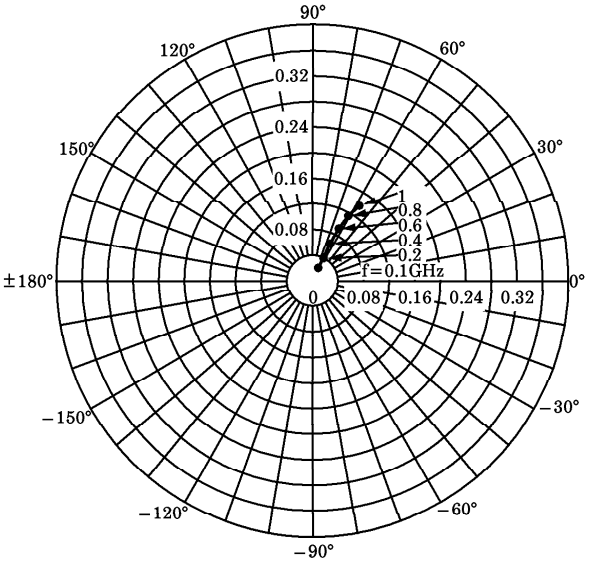
- The information contained herein is subject to change without notice.

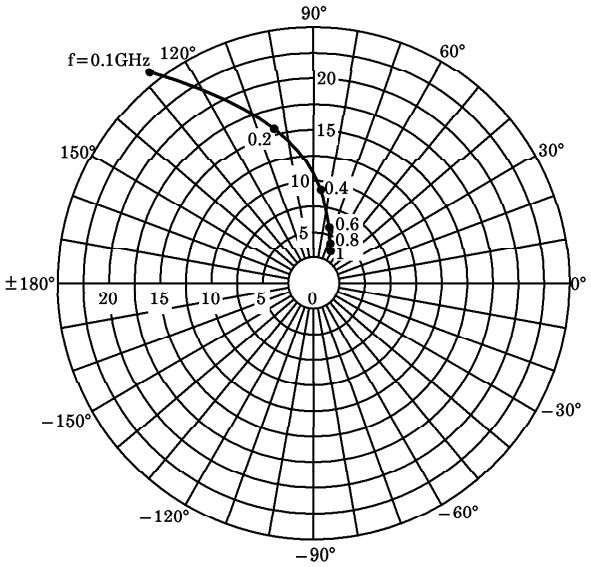
S_{11e}
V_{CE} = 10V
I_C = 20mA
Ta = 25°C
(UNIT : Ω)



S_{12e}
V_{CE} = 10V
I_C = 20mA
Ta = 25°C



S_{21e}
V_{CE} = 10V
I_C = 20mA
Ta = 25°C



S_{22e}
V_{CE} = 10V
I_C = 20mA
Ta = 25°C
(UNIT : Ω)